

MMBT3906K

PNP Epitaxial Silicon Transistor

General Purpose Transistor



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-200	mA
P _C	Collector Power Dissipation	350	mW
T _{J,} T _{STG}	Operating Junction and Storage Temperature Range	-55 ~ 150	°C

Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition		Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	-40		V
BV _{CEO}	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = -1.0 {\rm mA}, I_{\rm B} = 0$	-40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	-5		V
I _{CEX}	Collector Cut-off Current	$V_{CE} = -30V, V_{EB} = -3V$		-50	nA
h _{FE}	DC Current Gain *	$ \begin{array}{l} V_{CE} = -1V, \ I_{C} = -0.1mA \\ V_{CE} = -1V, \ I_{C} = -1mA \\ V_{CE} = -1V, \ I_{C} = -1mA \\ V_{CE} = -1V, \ I_{C} = -10mA \\ V_{CE} = -1V, \ I_{C} = -50mA \\ V_{CE} = -1V, \ I_{C} = -100mA \end{array} $	60 80 100 60 30	300	
V _{CE} (sat)	Collector-Emitter Saturation Voltage *	$I_{C} = -10mA, I_{B} = -1mA$ $I_{C} = -50mA, I_{B} = -5.0mA$		-0.25 -0.4	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage *	$I_{\rm C}$ = -10mA, $I_{\rm B}$ = -1.0mA $I_{\rm C}$ = -50mA, $I_{\rm B}$ = -5.0mA		-0.85 -0.95	V V
f _T	Current Gain Bandwidth Product	I _C = -10mA, V _{CE} = -20V, f = 100MHz 250			MHz
C _{ob}	Output Capacitance	V _{CB} = -5V, I _E =0, f=1.0MHz 4.5		4.5	pF
NF	Noise Figure	I_{C} = -100μA, V _{CE} = -5V, R _S = 1KΩ f = 10Hz to 15.7KHz		4	dB
t _{ON}	Turn On Time	$V_{CC} = -3V, V_{BE} = -0.5V$ $I_C = -10mA, I_{B1} = -1mA$ 70		70	ns
t _{OFF}	Turn Off Time	$V_{CC} = -3V, I_C = -10mA, I_{B1} = I_{B2} = -1mA$ 30		300	ns

* Pulse Test: Pulse Width ${\leq}300\mu s,$ Duty Cycle ${\leq}2\%$

Typical Performance Characteristics

Figure 1. DC current Gain

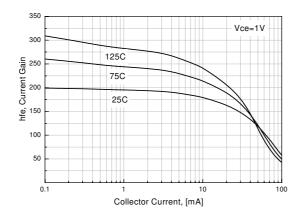


Figure 2. Collector-Emitter Saturation Voltage

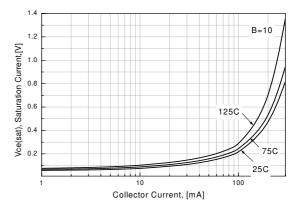
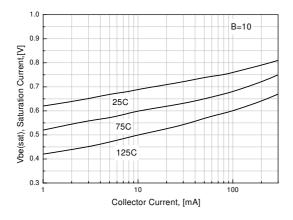


Figure 3. Base-Emitter Saturation Voltage





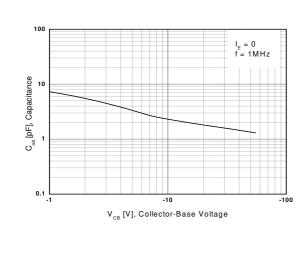
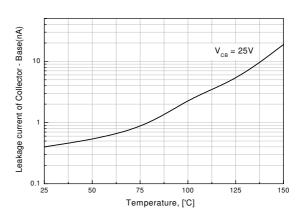
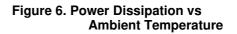
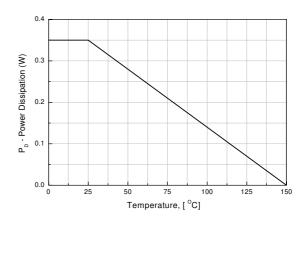
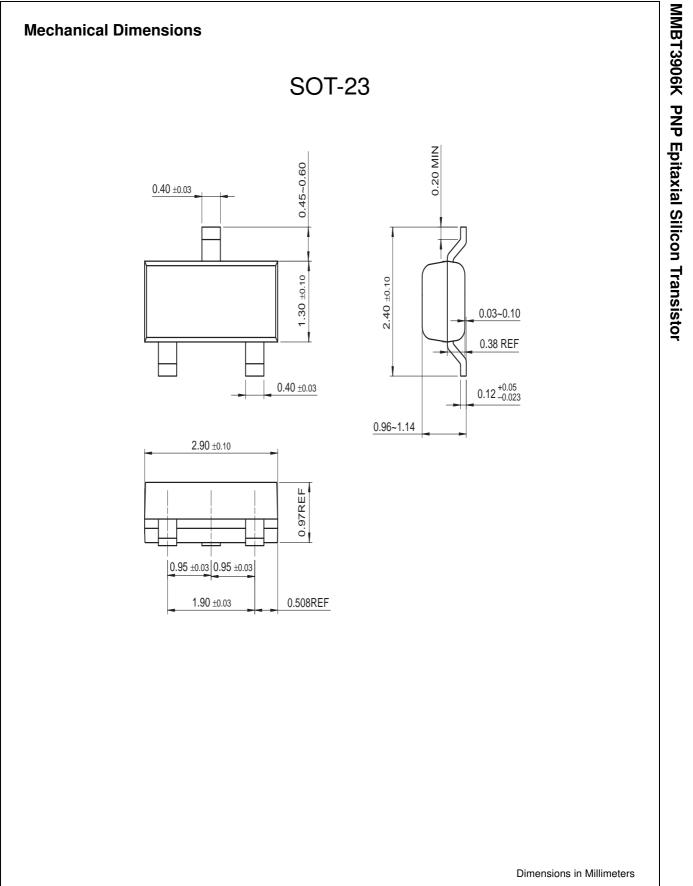


Figure 4. Collector - Base Leakage Current









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